TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT MULTI-CHIP

TD62M4503AFN

POWER MOS FET 4CH SINK DRIVER

TD62M4503AFN is 1CHIP 4ch FET Sink Driver built in Discrete Power MOS FET (2SK1078) × 4 and Diodes (1SS184).

FEATURES

- 4V Drive
- Low ON Resistance : R_{DS} (ON) = 0.58 Ω (Typ.)
- Low Leakage Current
 - : I_{GSS} = $\pm 3 \mu$ A (Max.) (V_{GS} = ± 16 V)
 - : I_{GSS} = 100 μ A (Max.) (V_{GS} = 60 V)
- Enhancement Type
 - : $V_{th} = 0.8 \sim 2.0 \text{ V} (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$
- Small Package : SSOP 24 (0.65 mm Pitch)



Weight: 0.14 g (Typ.)

BLOCK DIAGRAM



PIN CONNECTION (TOP VIEW)

		_	
1GATE	1	24] 3GATE
1GATE	2	23] 3GATE
1SOURCE	3	22	3SOURCE
NC	4	21] NC
1DRAIN	5	20	3DRAIN
2DRAIN	6	19	4DRAIN
NC	7	18] NC
2SOURCE	8	17	4\$OURCE
2GATE	9	16	4GATE
2DRAIN	10	15	d 4drain
CATHODE	11	14	CATHODE
ANODE1	12	13	ANODE2

NC: Non Connection

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Drain-Source Voltage		V _{DSS}	60	V	
Drain-Gate Voltage (R _{GS} = 20 kΩ)		V _{DGR}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current	DC	Ι _D	0.8	А	
	Pulse	I _{DP}	1.6	А	
Diode Reverse Voltage		V _R	80	V	
Diode Average Rectifier Current		Ι _Ο	0.1	А	
Power Dissipation	_	D-	0.78	W	
	(Note 1)	FD	0.89	W	
Junction Temperature		Tj	150	°C	
Operating Temperature		T _{opr}	-40~85	°C	
Storage Temperature		T _{stg}	-55~150	°C	

Note 1: On Glass Epoxy PCB (50 × 50 × 1.6 mm Cu 40%)

This device is an electrostatic sensitivity device. Please handle with caurion.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current	I _{GSS}	_	V_{GS} = ±16 V, V_{DS} = 0 V	_	_	±3	μA
Drain Cut-off Current	IDSS	_	V _{DS} = 60 V, V _{GS} = 0 V	_	_	100	μA
Drain Source Braeakdown Voltage	V (BR) DSS	—	I _D = 10 mA, V _{GS} = 0 V	60	—	—	V
Gate Thresold Voltage	V _{th}	—	V _{DS} = 10 V, I _D = 1 mA	0.8	—	2.0	V
Drain ON Current	I _{D (ON)}	—	V _{DS} = 4 V, V _{GS} = 4 V	0.8	—	—	А
Drain-Source ON Resistance	R _{DS (ON)}	-	V _{GS} = 4 V, I _D = 0.4 A		0.75	1.1	Ω
Dialit-Source On Resistance			V_{GS} = 10 V, I _D = 0.4 A		0.58	0.70	Ω
	V _{F (1)}	_	I _F = 1 mA		0.60	_	
Diode Forward Voltage	V _{F (2)}	_	I _F = 10 mA		0.72	_	V
	V _{F (3)}	—	I _F = 100 mA	_	1.0	1.4	
Diode Reverse Current	I _{R (1)}	—	V _R = 30 V	_	—	0.1	μA
	I _{R (2)}		V _R = 80 V	_	_	0.5	μA

PRECAUTIONS for USING

This IC does not integrate protection circuits such as overcurrent and overvoltage protectors. Thus, if excess current or voltage is applied to the IC, the IC may be damaged. Please design the IC so that excess current or voltage will not be applied to the IC.

Utmost care is necessary in the design of the output line, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

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PACKAGE DIMENSIONS



Weight: 0.14 g (Typ.)

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